

# isc Silicon NPN Power Transistor

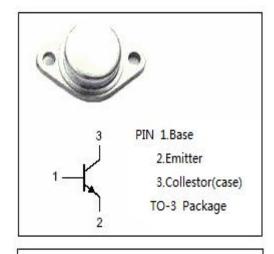
2SD113

## DESCRIPTION

- · Collector-Emitter Breakdown Voltage-
  - : V<sub>(BR)CEO</sub>= 80V (Min)
- · High Power Dissipation
- · High Current Capability
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

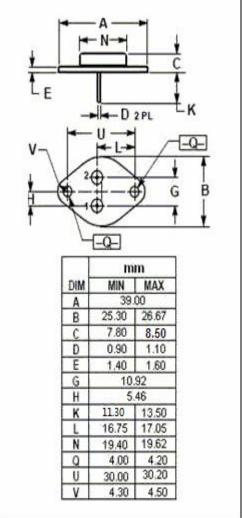
#### **APPLICATIONS**

- · Audio power amplifier, power switching applications.
- · DC-DC converter and regulator applications.



# ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	MAX	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	100	V
V <sub>CEO</sub>	Collector-Emitter Voltage	80	V
V <sub>EBO</sub>	Emitter-Base Voltage 10		V
Ic	Collector Current-Continuous	30	Α
l <sub>E</sub>	Emitter Current-Continuous	30	Α
I <sub>B</sub>	Base Current-Continuous 5		Α
P <sub>C</sub>	Collector Power Dissipation @T <sub>C</sub> =25°C 200		W
T <sub>j</sub>	Junction Temperature 150		$^{\circ}$ C
T <sub>stg</sub>	Storage Temperature Range -65~150		°C





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#### **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector- Emitte Breakdown Voltage	I <sub>C</sub> = 10mA; R <sub>BE</sub> = ∞	80			V
V <sub>(BR)EBO</sub>	Emitte - Base Breakdown Voltage	I <sub>E</sub> = 1mA; I <sub>C</sub> = 0	10			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 15A; I <sub>B</sub> = 3A			1.5	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 15A; I <sub>B</sub> = 3A			2.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 50V; I <sub>E</sub> = 0			2	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 10V; I <sub>C</sub> = 0			50	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 5V	50		300	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 15A; V <sub>CE</sub> = 5V	10			
Сов	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 50V; f <sub>test</sub> = 1.0MHz		400		pF
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 1A; V <sub>CE</sub> = 10V		1.5		MHz

### h<sub>FE-1</sub> Classifications

0	Y		
50-150	100-300		

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